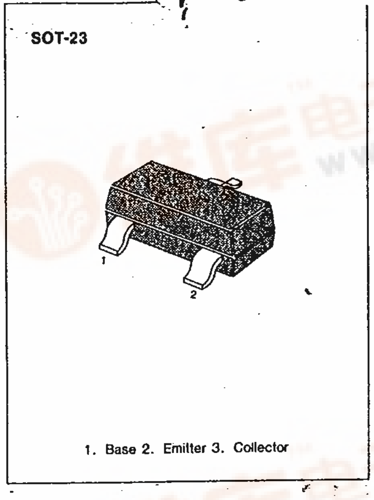
MMBA812M5 PNP EPITAXIAL SILICON TRANSISTOR

T-27-09

GENERAL PURPOSE TRANSISTOR



ABSOLUTE MAXIMUM RATINGS ($T_a=25°C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

- Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS ($T_a=25°C$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=40V$, $I_E=0$		100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V$, $I_C=0$		100	nA
DC Current Gain	h_{FE}	$V_{CE}=6V$, $I_C=1mA$	135	270	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	$I_C=30mA$, $I_B=3mA$		0.5	V
Base-Emitter On Voltage	V_{BE} (on)	$I_C=1mA$, $V_{CE}=6V$		0.8	V

Marking